

TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

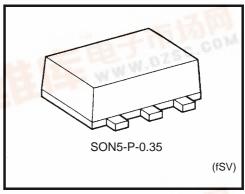
TC7SH125FS

Bus Buffer

Features

High speed: $t_{pd}=3.8$ ns (typ.) at $V_{CC}=5$ V Low power dissipation: $I_{CC}=2$ μ A (max) at Ta = 25°C High noise immunity: $V_{NIH}=V_{NIL}=28\%$ V_{CC} (min) 5.5V tolerant input.

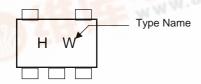
Wide operating voltage range: V_{CC} (opr) = 2~5.5 V



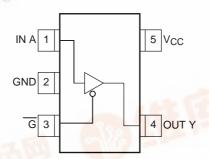
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Weight: 0.001 g (Typ.)

Marking



Pin Assignment (top view)





Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Supply voltage range	V _{CC}	-0.5~7.0	V
DC input voltage	V _{IN}	-0.5~7.0	V
DC output voltage	V _{OUT}	−0.5~V _{CC} + 0.5	٧
Input diode current	I _{IK}	-20	mA
Output diode current	lok	±20	mA
DC output current	lout	±25	mA
DC V _{CC} /ground current	Icc	±50	mA
Power dissipation	PD	50	mW
Storage temperature	T _{stg}	-65~150	°C

Logic Diagram



Truth Table

G	Α	Υ
Н	Х	Z
L	L	L
L	Н	Н

Recommended Operating Conditions

Characteristics	Symbol	Rating	Unit
Supply voltage	V _{CC}	2.0~5.5	V
Input voltage	V _{IN}	0~5.5	V
Output voltage	V _{OUT}	0~Vcc	V
Operating temperature	T _{opr}	-40~85	°C
Input rise and fall time	dt/dv	$0 \sim 100 \; (V_{CC} = 3.3 \pm 0.3 \; V)$	ns/V
	ui/dv	0~20 (V _{CC} = 5 ± 0.5 V)	115/ V

Electrical Characteristics

DC Characteristics

Characteristics Symbol Test Circuit		Test	at l			Ta = 25°C		Ta = -40~85°C				
		Test Condition		V _{CC} (V)	Min	Тур.	Max	Min	Max	Unit		
High-level input				2.0	1.5	_	_	1.5	_			
voltage	V _{IH}			_		V _{CC} × 0.7	_	_	V _{CC} × 0.7	_	V	
Low-level input			_		2.0	_	_	0.50	_	0.50	V	
voltage	V_{IL}	_			3.0~ 5.5	_	_	V _{CC} × 0.3	_	V _{CC} × 0.3		
			V _{IN} = V _{IH}	Ι _{ΟΗ} = -50 μΑ	2.0	1.9	2.0	_	1.9	_	V	
High-level VOH					3.0	2.9	3.0	_	2.9	_		
	V_{OH}	_			4.5	4.4	4.5	_	4.4	_		
				I _{OH} = -4 mA	3.0	2.58	_	_	2.48	_		
				I _{OH} = -8 mA	4.5	3.94	_	_	3.80	_		
					2.0	_	0	0.1	_	0.1		
			$I_{OL} = 50 \mu A$	3.0	_	0	0.1	_	0.1			
Low-level output voltage	V_{OL}	_	$V_{IN} = V_{IH} \\$		4.5	_	0	0.1	_	0.1	V	
				I _{OL} = 4 mA	3.0	_	_	0.36	—	0.44		
				I _{OL} = 8 mA	4.5		_	0.36	—	0.44		
3-state output off-state current	l _{OZ}	_	V _{IN} = V _{IH} or V _{IL} V _{OUT} = V _{CC} or GND		5.5	_	_	±0.25	_	±2.5	μА	
Input leakage current	I _{IN}	_	V _{IN} = 5.5 V or GND		0~ 5.5	_	_	±0.1	_	±1.0	μΑ	
Quiescent supply current	Icc		V _{IN} = V _{CC} or GND				_	2.0	_	20.0	μА	

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AC Characteristics (Input: $t_r = t_f = 3$ ns)

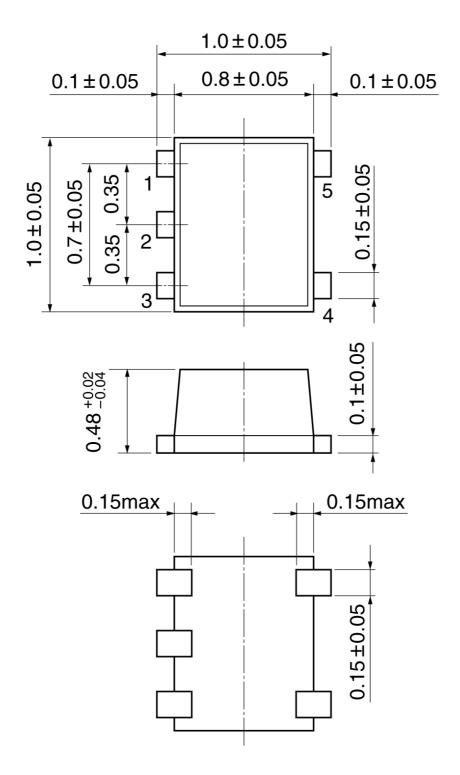
Characteristics	Symbol	Test	Test Condition		Ta = 25°C			Ta = -40~85°C		Unit	
Characteristics Symbo	Symbol	Circuit	Circuit	V _{CC} (V)	C _L (pF)	Min	Тур.	Max	Min	Max	Offic
	t _{pLH}		_	3.3 ± 0.3	15	_	5.6	8.0	1.0	9.5	ns ns
Propagation delay		_			50	_	8.1	11.5	1.0	13.0	
time	t_{pHL}			5.0 ± 0.5	15	_	3.8	5.5	1.0	6.5	
					50	_	5.3	7.5	1.0	8.5	
3-state output enable time	^t pZL			3.3 ± 0.3	15	_	5.4	8.0	1.0	9.5	- ns
					50	_	7.9	11.5	1.0	13.0	
	t _{pZH}	_		5.0 ± 0.5	15	_	3.6	5.1	1.0	6.0	
				5.0 ± 0.5	50	_	5.1	7.1	1.0	8.0	
3-state output disable time	t _{pLZ}			3.3 ± 0.3	50	_	9.5	13.2	1.0	15.0	ns
	t _{pHZ}	_	_	5.0 ± 0.5	50	_	6.1	8.8	1.0	10.0	115
Input capacitance	C _{IN}	_		_		_	4	10	_	10	pF
Output capacitance	C _{OUT}	_		_		_	6	_	_	_	pF
Power dissipation capacitance	C _{PD}	_			(Note)	_	14	_	_	_	pF

Note: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

$$I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$$

Package Dimensions



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Weight: 0.001 g (typ.)

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